

April 2010

2N7002V/VA

N-Channel Enhancement Mode Field Effect Transistor

Features

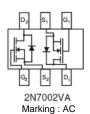
- Dual N-Channel MOSFET
- · Low On-Resistance
- · Low Gate Threshold Voltage
- · Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- · Lead Free By Design/RoHS Compliant



SOT-563F* Pin1 and Pin4 are exchangeable.



2N7002V Marking : AB



Absolute Maximum Ratings * T_A = 25℃ unless otherwise noted

Symbol	Parameter		Value	Units
V _{DSS}	Drain-Source Voltage		60	V
V_{DGR}	Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		60	V
V_{GSS}	Gate-Source Voltage	Continuous Pulsed	±20 ±40	V
I _D	Drain Current	Continuous Pulsed	280 1.5	mA A
T _J , T _{STG}	Junction and Storage Temperature Range		-55 to +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units	
P _D	Total Device Dissipation Derating above $T_A = 25^{\circ}$	250 2.0	mW mW/℃	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient *	500	°C/W	

^{*} Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch, Minimum land pad size.

Electrical Characteristics $T_A = 25\%$ unless otherwise noted

Parameter	Test Condition	Min.	Тур.	Max.	Units
cteristics (Note1)			•		•
Drain-Source Breakdown Voltage	V_{GS} =0V, I_D =10 μ A	60	78	-	V
Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V V _{DS} =60V, V _{GS} =0V, @T _C =125°C	-	0.001 7	1.0 500	μА
Gate-Body Leakage	V _{GS} =±20V, V _{DS} =0V	-	0.2	±100	nA
cteristics (Note1)					
Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.76	2.5	V
Static Drain-Source On-Resistance	V_{GS} =5V, I_D =0.05A, V_{GS} =10V, I_D =0.5A, @T _J =125°C	-	1.6 2.53	7.5 13.5	Ω
On-State Drain Current	V _{GS} =10V, V _{DS} =7.5V	0.5	1.43	-	Α
Forward Transconductance	V _{DS} =10V, I _D =0.2A	80	356.5	-	mS
Characteristics					
Input Capacitance		-	37.8	50	pF
Output Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	12.4	25	pF
Reverse Transfer Capacitance		-	6.5	7.0	pF
Characteristics					
Turn-On Delay Time	V _{DD} =30V, I _D =0.2A, V _{GEN} =10V	-	5.85	20	ns
Turn-Off Delay Time	$R_L=150\Omega$, $R_{GEN}=25\Omega$	-	12.5	20	113
	Drain-Source Breakdown Voltage Zero Gate Voltage Drain Current Gate-Body Leakage Eteristics (Note1) Gate Threshold Voltage Static Drain-Source On-Resistance On-State Drain Current Forward Transconductance Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance Characteristics Turn-On Delay Time	Cteristics (Note1)Drain-Source Breakdown VoltageVGS=0V, ID=10μAZero Gate Voltage Drain CurrentVDS=60V, VGS=0V VDS=60V, VGS=0V, @TC=125°CGate-Body LeakageVGS=±20V, VDS=0VCteristics (Note1)VDS=VGS, ID=250μAGate Threshold VoltageVDS=VGS, ID=250μAStatic Drain-SourceVGS=5V, ID=0.05A, WGS=10V, ID=0.5A, @TJ=125°COn-ResistanceVGS=10V, VDS=7.5VForward TransconductanceVDS=10V, ID=0.2ACharacteristicsInput CapacitanceOutput CapacitanceVDS=25V, VGS=0V, f=1.0MHzReverse Transfer CapacitanceVDS=30V, ID=0.2A, VGEN=10VCharacteristicsTurn-On Delay TimeVDD=30V, ID=0.2A, VGEN=10V	Drain-Source Breakdown Voltage V _{GS} =0V, I _D =10μA 60 Zero Gate Voltage Drain Current V _{DS} =60V, V _{GS} =0V -	Drain-Source Breakdown Voltage V _{GS} =0V, I _D =10μA 60 78	Drain-Source Breakdown Voltage V _{GS} =0V, I _D =10μA 60 78 -

Note1 : Short duration test pulse used to minimize self-heating effect.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

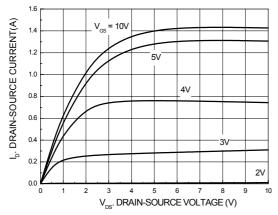


Figure 3. On-Resistance Variation with

Temperature

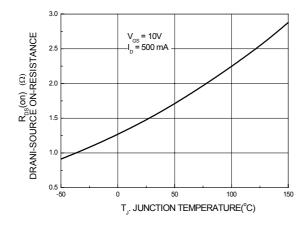


Figure 5. Transfer Characteristics

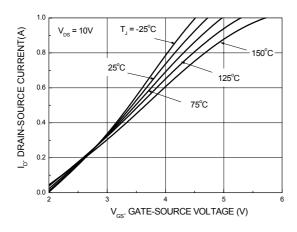


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

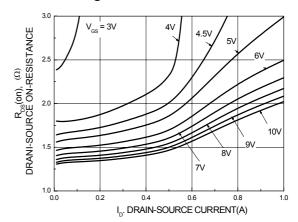


Figure 4. On-Resistance Variation with Gate-Source Voltage

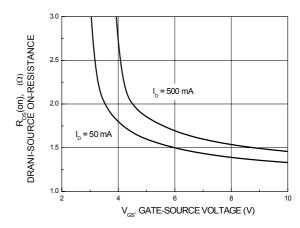
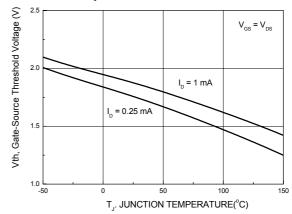


Figure 6. Gate Threshold Variation with Temperature



Typical Performance Characteristics

Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

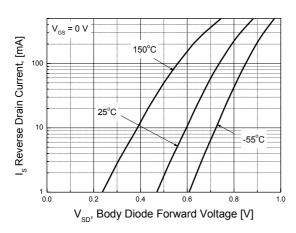
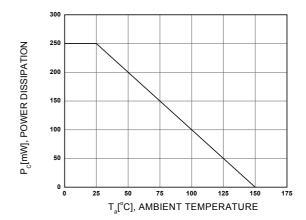
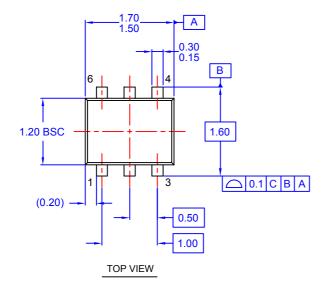


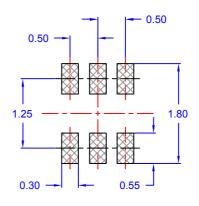
Figure 8. Power Derating



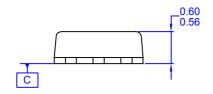
Package Dimensions

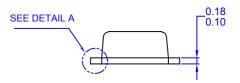
SOT-563F

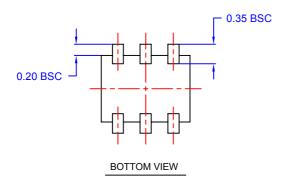


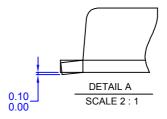


LAND PATTERN RECOMMENDATION









Dimensions in Millimeters





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Definition of Terms				
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